

Features

- Low reverse current
- Good surge current capability
- Low capacitive charge
- No reverse recovery current

V_{RRM}	=	650	V
$I_F (T_C=135^\circ C)$	=	10	A
Q_c	=	30	nC

Benefits

- System efficiency improvement over Si diodes
- Higher switching frequency
- Increased power density
- Essentially no switching losses

Package



TO-220-2F

Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- On Board Charger
- UPS



Part Number	Package	Marking
ASZD010065F	TO-220-2F	ASZD010065F

Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Test conditions	Value	Unit
V _{RRM}	Repetitive peak reverse voltage		650	V
V _{RSM}	Non-repetitive peak reverse voltage		650	V
I _F	Continuous forward current	T _c =25°C T _c =100°C T _c =135°C	23 15 10	A
I _{FRM}	Repetitive forward surge current	T _c =25°C , t _p =10ms, Half Sine Pulse T _c =110°C , t _p =10ms, Half Sine Pulse	45 27	A
I _{FSM}	Non-Repetitive forward surge current	T _c =25°C , t _p =10ms, Half Sine Pulse T _c =110°C , t _p =10ms, Half Sine Pulse	80 70	A
∫i ² dt	i ² t value	T _c =25°C , t _p =10ms, Half Sine Pulse T _c =110°C , t _p =10ms, Half Sine Pulse	31.7 24.3	A ² S
P _{tot}	Power dissipation	T _c =25°C T _c =110°C	59 26	W
T _j	Operating junction temperature		-55~175	°C
T _{stg}	Storage temperature		-55~150	°C

Electrical Characteristics (T_j=25°C unless otherwise specified)
Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V _{DC}	DC blocking voltage	T _j =25°C	650			V
V _F	Diode forward voltage	I _F =10A T _j =25°C I _F =10A T _j =175°C		1.35 1.60	1.60	V
I _R	Reverse current	V _R =650V T _j =25°C V _R =650V T _j =175°C			50 200	μA

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q _C	Total capacitive charge	V _R =400V T _j =25°C $Q_C = \int_0^{VR} C(V)dV$		30		nC
C	Total capacitance	V _R =0V f=1MHz V _R =200V f=1MHz V _R =400V f=1MHz		550 58 51		pF
E _C	Capacitance stored energy	V _R =400V		8		μJ

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
R _{th(jc)}	Thermal resistance from junction to case		2.54		°C/W

Electrical Characteristic Curves

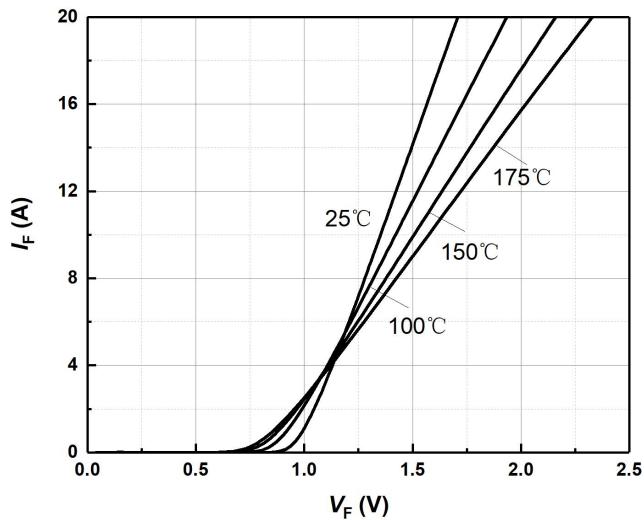


Figure 1. Typical forward characteristics

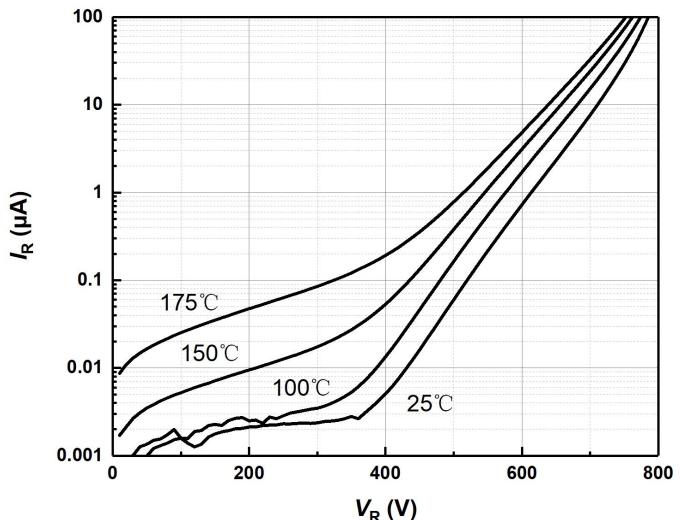


Figure 2. Typical reverse current as function of reverse voltage

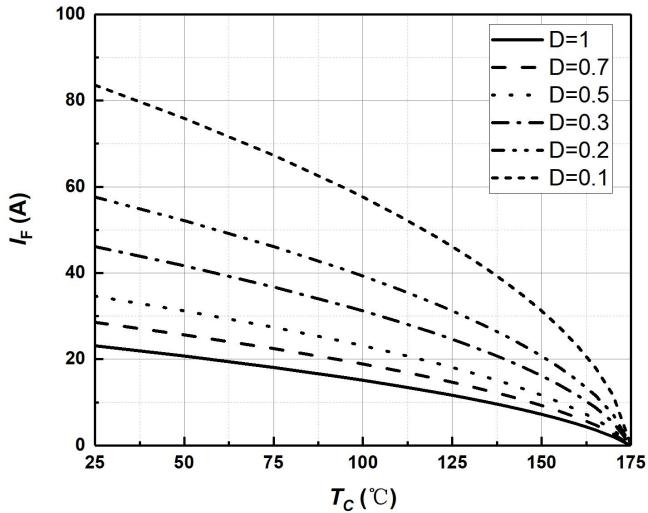


Figure 3. Diode forward current as function of temperature, D=duty cycle

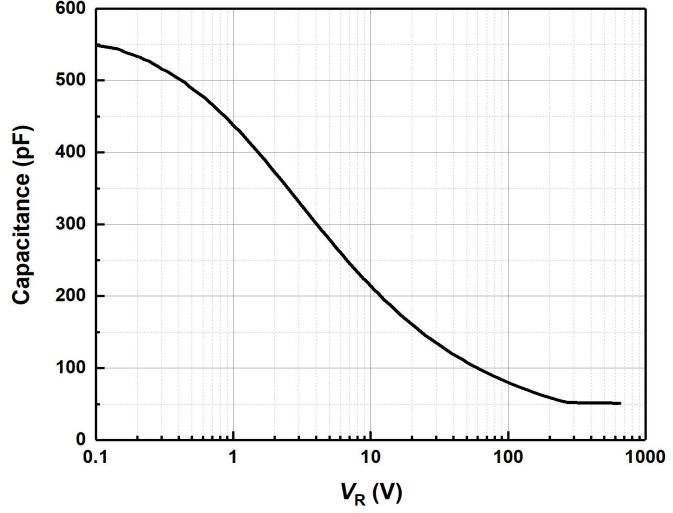


Figure 4. Typical capacitance as function of reverse voltage $C=f(V_R)$; $T_j=25^\circ\text{C}$

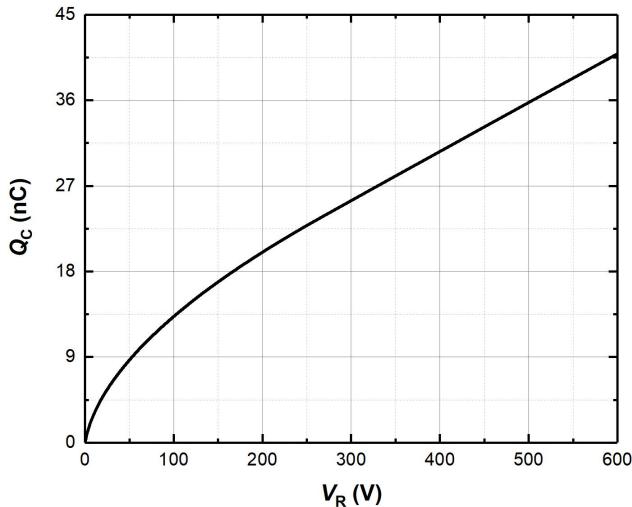


Figure 5. Typical reverse charge as function of reverse voltage

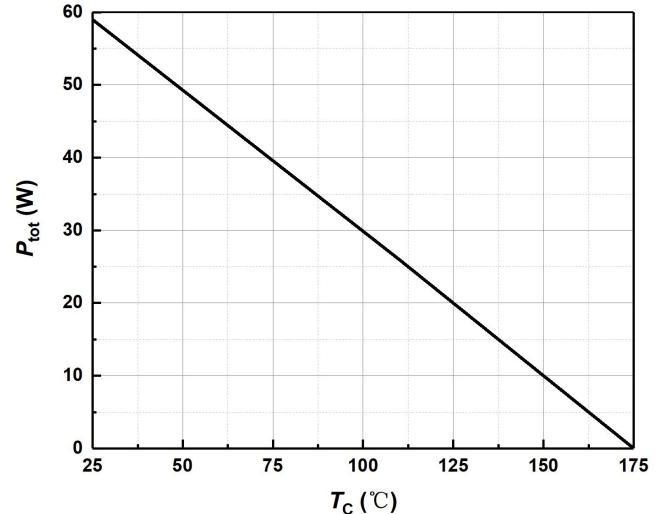
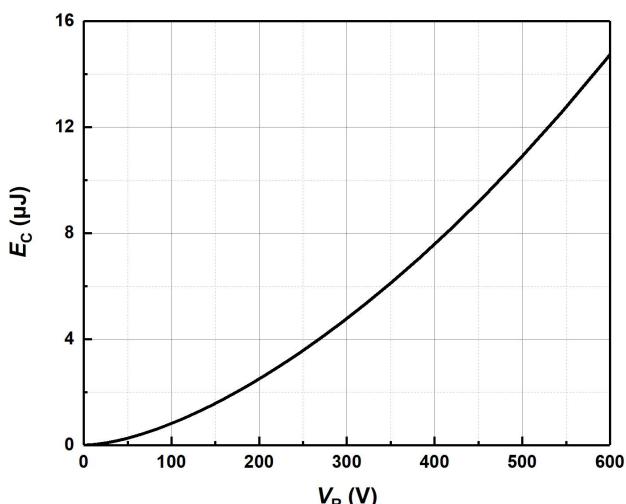
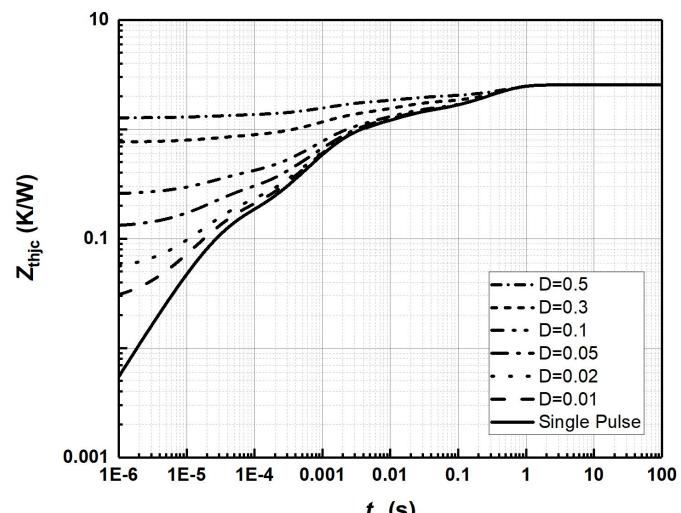
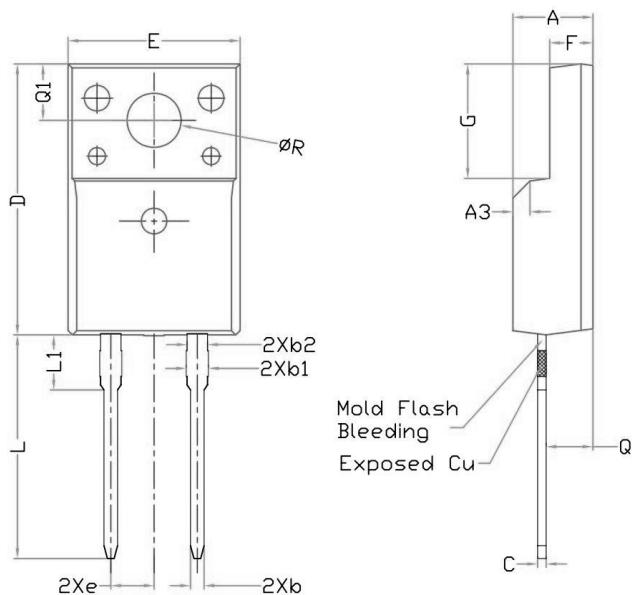


Figure 6. Power dissipation as function of case temperature

Electrical Characteristic Curves**Figure 7. Capacitance stored energy****Figure 8. Max. transient thermal impedance**

Package Dimensions

Package TO-220-2F



SYMBOL	DIMENSIONS		
	Min.	Nom.	Max.
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e	2.54		
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
ΦR	3.08	3.18	3.28